

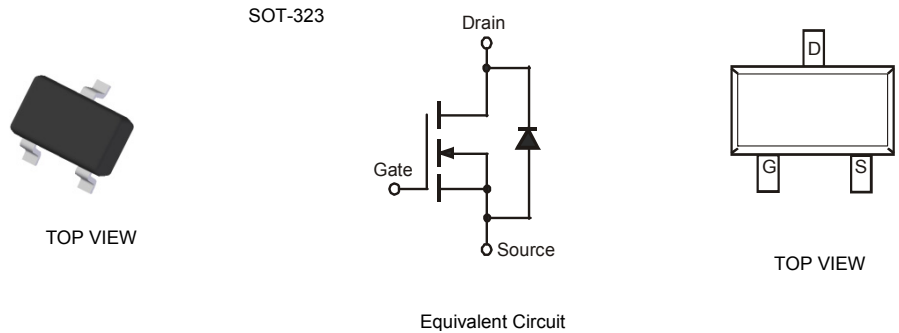
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low-On Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

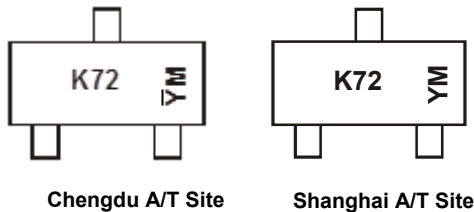


Ordering Information (Notes 4)

Part Number	Case	Packaging
2N7002W-7-F	SOT-323	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



K72 = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or Y̅ = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Year	2012	2013	2014	2015	2016	2017	2018
Code	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ	V _{DGR}	60	V
Gain-Source Voltage	V _{GSS}	±20	V
		±40	
Drain Current (Note 5)	I _D	115	mA
		73	
		800	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	200	mW
Derating above T _A = +25°C		1.60	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current @ T _C = +125°C	I _{DSS}	—	—	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance @ T _J = +125°C	R _{DS(ON)}	—	1.8	7.5	Ω	V _{GS} = 5.0V, I _D = 0.05A
		—	2.6	13.5		V _{GS} = 10V, I _D = 0.5A
On-State Drain Current	I _{D(ON)}	0.5	1.0	—	A	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} = 10V, I _D = 0.2A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{ISS}	—	22	50	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	11	25	pF	
Reverse Transfer Capacitance	C _{RSS}	—	2.0	5.0	pF	
SWITCHING CHARACTERISTICS (Note 7)						
Turn-On Delay Time	t _{D(ON)}	—	7.0	20	ns	V _{DD} = 30V, I _D = 0.2A, R _L = 150Ω, V _{GEN} = 10V, R _{GEN} = 25Ω
Turn-Off Delay Time	t _{D(OFF)}	—	11	20	ns	

- Notes:
- Device mounted on FR-4 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

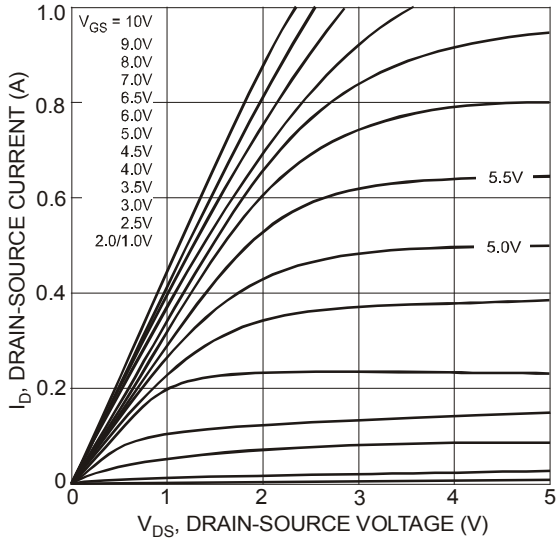


Fig. 1 On-Region Characteristics

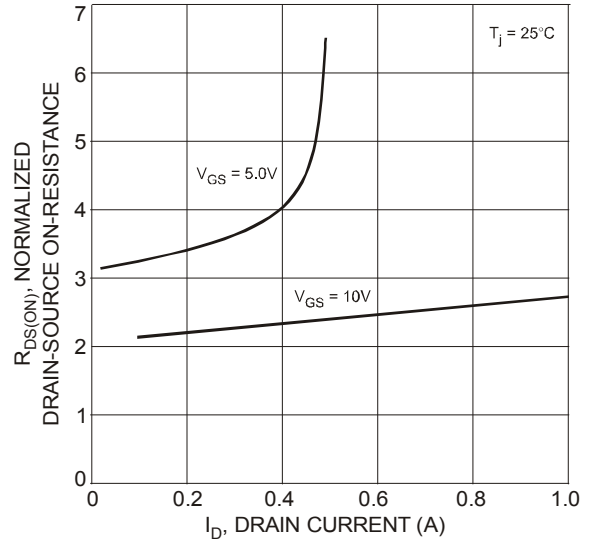


Fig. 2 On-Resistance vs. Drain Current

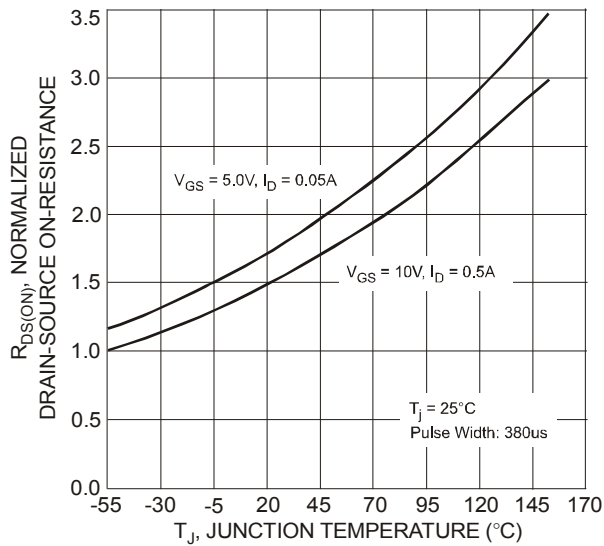


Fig. 3 On-Resistance vs. Junction Temperature

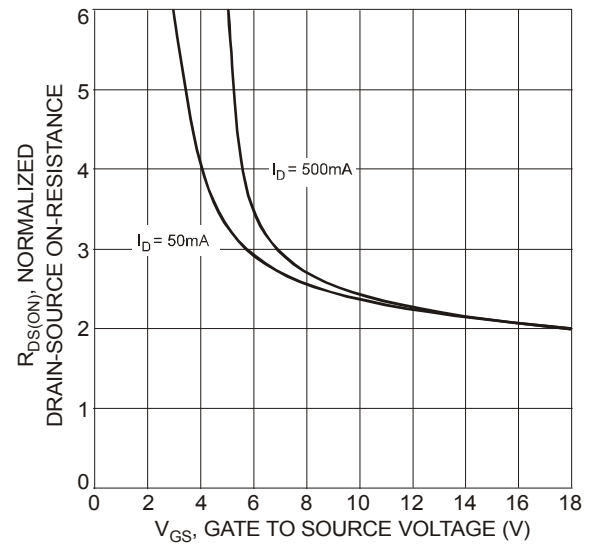
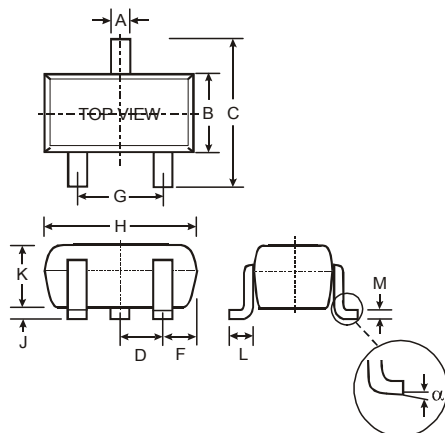


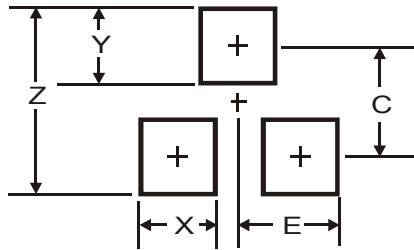
Fig. 4 On-Resistance vs. Gate-Source Voltage

Package Outline Dimensions



SOT-323		
Dim	Min	Max
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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